AR-P 6200 (CSAR 62) Resist

AR-P 6200 is a positive tone electron beam resist with high resolution and excellent dry-etching resistance

Characteristics:

- Positive tone
- High resolution
- High sensitivity
- Dry etch resistance comparable to most positive photo resists
- Not sensitive to white light

Resist available at TNFC	AR-P 6200.13
Storage	8-12 ºC
Surface Preparation	In general, no surface preparation aside from normal cleaning is necessary. Excellent adhesion to most surfaces.
Spin	Speed 1000-6000 rpm, 60 sec. (300-700 nm)
Pre-bake	150°C hotplate, 1 min. May also be oven baked at 150°C for 30 min.
Expose	Dose around 300 $\mu C/cm^2$ at 100 kV.
Develop	Amyl Acetate, 2 min
Rinse	IPA, 30 sec
Dry	By dry N_2
Post-Bake	Not normally necessary.
Descum	Oxygen plasma asher
Stripping	AR 600-71, possible heated; Oxygen plasma ashing

Link to AR-P 6200 manufacturer's data sheet:

http://tnfc.utoronto.ca/wp-content/uploads/2019/03/Allresist_Resist_ar-p6200_english.pdf